

B1  
conceded  
Sub C1 > ~~layer of the plurality of different material layers is selectively etchable with respect to the etch stop layer; and~~

~~patterning an interconnection to the contact point.~~

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Sub C3 >  
B2  
~~8. (Amended) A method comprising:  
introducing an etch stop layer over a substrate;  
introducing a dielectric layer over the etch stop layer between an  
interconnection line and a contact point on the substrate, the dielectric layer  
comprising a plurality of alternating material layers, wherein each respective  
layer of the plurality of alternating material layers is selectively etchable with  
respect to the etch stop layer; and~~

~~patterning an interconnection to the substrate.~~

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Please add the following new claims:

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--24. (New) The method of claim 1, wherein the etch stop layer is silicon nitride.

25. (New) The method of claim 8, wherein the etch stop layer is silicon nitride.

B3  
26. (New) The method of claim 1, wherein the plurality of different material layers includes at least one layer of silicon oxynitride.

27. (New) The method of claim 8, wherein the plurality of alternating material layers comprises alternating silicon oxynitride layers with at least one other material layer.--

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